

MC74HCT04A

Hex Inverter

With LSTTL-Compatible Inputs High-Performance Silicon-Gate CMOS

The MC74HCT04A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT04A is identical in pinout to the LS04.

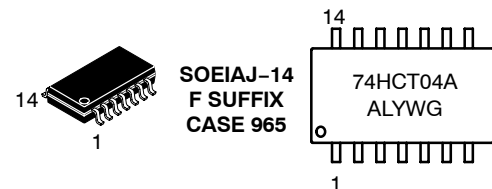
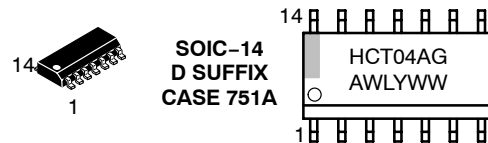
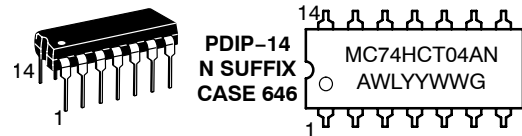
Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1 μ A
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- Pb-Free Packages are Available



ON Semiconductor®

MARKING DIAGRAMS



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G or ▪ = Pb-Free Package

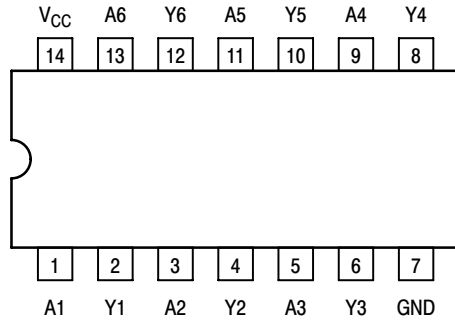
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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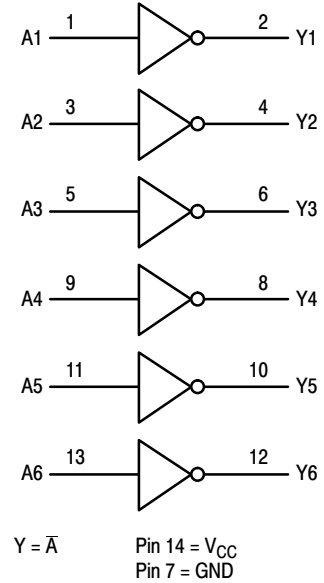
Pinout: 14-Lead Packages (Top View)



FUNCTION TABLE

Inputs	Outputs
A	Y
L	H
H	L

LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT04AN	PDIP-14	25 Units / Rail
MC74HCT04ANG	PDIP-14 (Pb-Free)	
MC74HCT04AD	SOIC-14	55 Units / Rail
MC74HCT04ADG	SOIC-14 (Pb-Free)	
MC74HCT04ADR2	SOIC-14	2500 / Tape & Reel
MC74HCT04ADR2G	SOIC-14 (Pb-Free)	
MC74HCT04ADTR2	TSSOP-14*	
MC74HCT04ADTR2G	TSSOP-14*	
MC74HCT04AFEL	SOEIAJ-14	2000 / Tape & Reel
MC74HCT04AFELG	SOEIAJ-14 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air	750	mW
	Plastic DIP†	500	
	SOIC Package† TSSOP Package†	450	
T_{stg}	Storage Temperature Range	- 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types	- 55	+ 125	°C
t_r, t_f	Input Rise/Fall Time (Figure 1)	0	500	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} V	Guaranteed Limit			Unit
				-55 to 25°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ $ I_{out} \leq 20\mu A$	4.5	2.0	2.0	2.0	V
			5.5	2.0	2.0	2.0	
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = V_{CC} - 0.1V$ $ I_{out} \leq 20\mu A$	4.5	0.8	0.8	0.8	V
			5.5	0.8	0.8	0.8	
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \leq 20\mu A$	4.5	4.4	4.4	4.4	V
			5.5	5.4	5.4	5.4	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \leq 20\mu A$	4.5	0.1	0.1	0.1	V
			5.5	0.1	0.1	0.1	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	4.5	0.26	0.33	0.40	μA
			5.5	±0.1	±1.0	±1.0	
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	4.5	1	10	40	μA
			5.5	1	10	40	
ΔI_{CC}	Additional Quiescent Supply Current	$V_{in} = 2.4V$, Any One Input $V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0\mu A$	5.5	≥ -55°C	25 to 125°C		mA
				2.9	2.4		

- Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

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AC CHARACTERISTICS ($V_{CC} = 5.0V \pm 10\%$, $C_L = 50pF$, Input $t_r = t_f = 6ns$)

Symbol	Parameter	Guaranteed Limit			Unit
		-55 to 25°C	≤85°C	≤125°C	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	15 17	19 21	22 26	ns
t_{TLH} , t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	15	19	22	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF

3. For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C_{PD}	Power Dissipation Capacitance (Per Inverter)*	Typical @ 25°C, $V_{CC} = 5.0 V$		pF
		22		

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

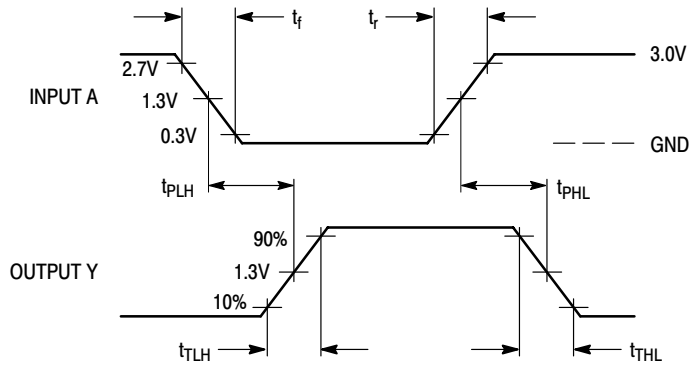
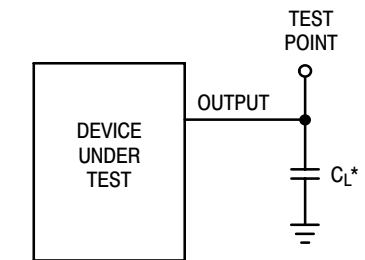


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

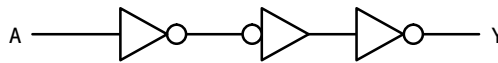
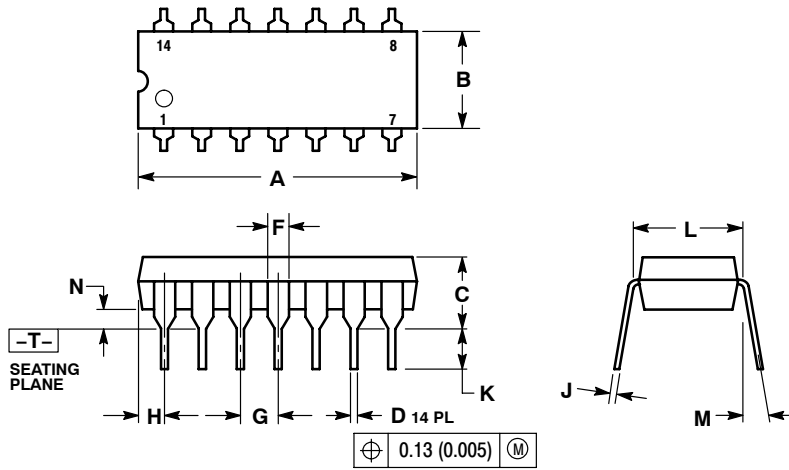


Figure 3. Expanded Logic Diagram
(1/6 of the Device Shown)

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PACKAGE DIMENSIONS

PDIP-14
CASE 646-06
ISSUE P



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---	10°	---	10°
N	0.015	0.039	0.38	1.01